MR2502, MR2504, MR2510

MR2504 and MR2510 are Preferred Devices

Medium-Current Silicon Rectifiers

. . . compact, highly efficient silicon rectifiers for medium–current applications requiring:

- High Current Surge — 400 Amperes @ T_J = 175°C
- Peak Performance @ Elevated Temperature — 25 Amperes @ T_C = 150°C
- Low Cost
- Compact, Molded Package — For Optimum Efficiency in a Small Case Configuration

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.8 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminals are Readily Solderable
- Lead Temperature for Soldering Purposes: requires a custom temperature soldering profile
- Polarity: Cathode Polarity Band
- Shipped 5000 units per box

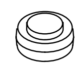
MAXIMUM RATINGS

Please See the Table on the Following Page

ON Semiconductor™

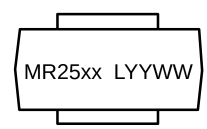
http://onsemi.com

MEDIUM–CURRENT SILICON RECTIFIERS 25 AMPERES 200–1000 VOLTS DIFFUSED JUNCTION



MICRODE BUTTON CASE 193

MARKING DIAGRAM



MR25xx = Device Code
xx = 02, 04 or 10
L = Location Code
YY = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MR2502	Microde Button	5000 Units/Box
MR2504	Microde Button	5000 Units/Box
MR2510	Microde Button	5000 Units/Box

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Characteristic	Symbol	MR2502	MR2504	MR2510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	200	400	1000	Volts
Non–Repetitive Peak Reverse Voltage (Halfwave, single phase, 60 Hz peak)	V_{RSM}	240	480	1200	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, T_C = 150°C)	I_O	25			Amps
Non–Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	400 (for 1 cycle)			Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}	– 65 to +175			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (Single Side Cooled)	$R_{\theta JC}$	1.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (i_F = 78.5 Amps, T_C = 25°C)	v_F	1.18	Volts
Maximum Reverse Current (rated dc voltage) T_C = 25°C T_C = 100°C	I_R	 100 500	µA

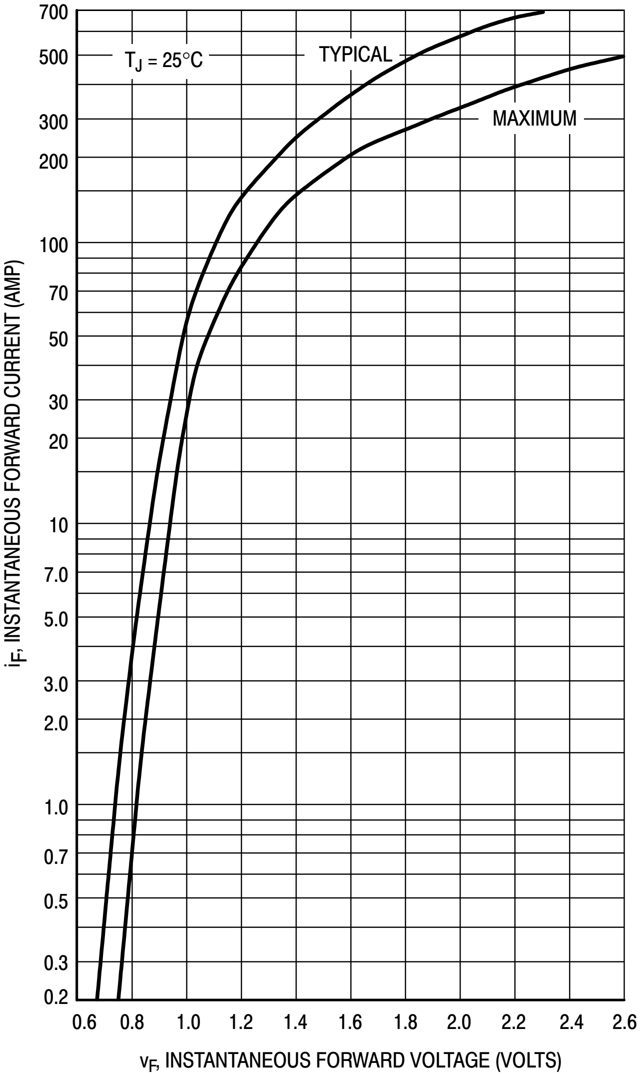


Figure 1. Forward Voltage

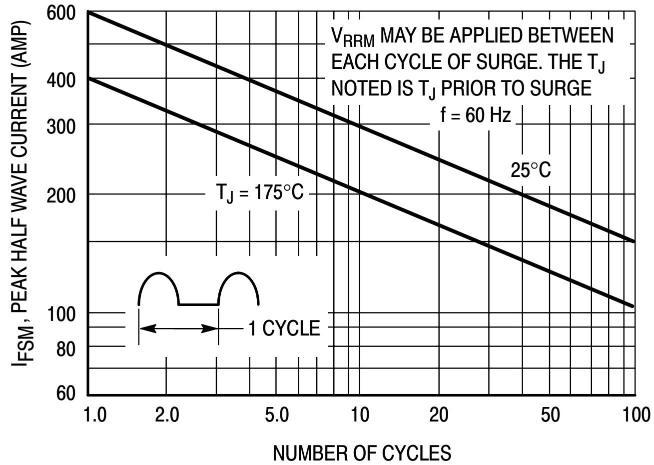


Figure 2. Non–Repetitive Surge Current

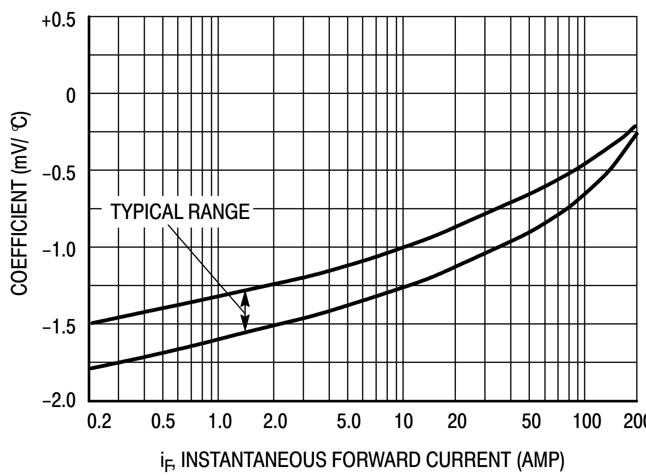


Figure 3. Forward Voltage Temperature Coefficient

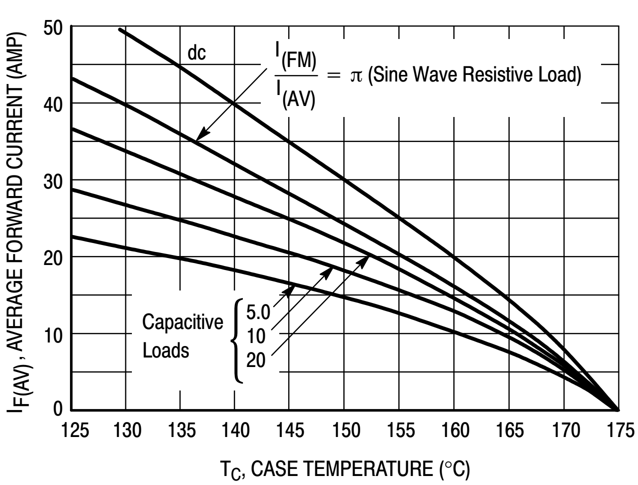


Figure 4. Current Derating

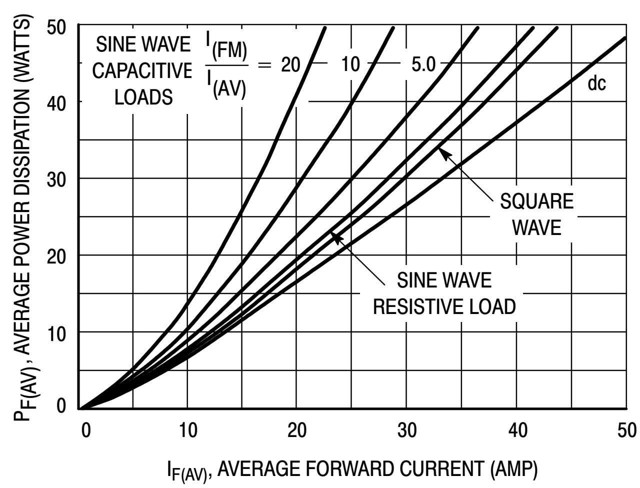


Figure 5. Forward Power Dissipation

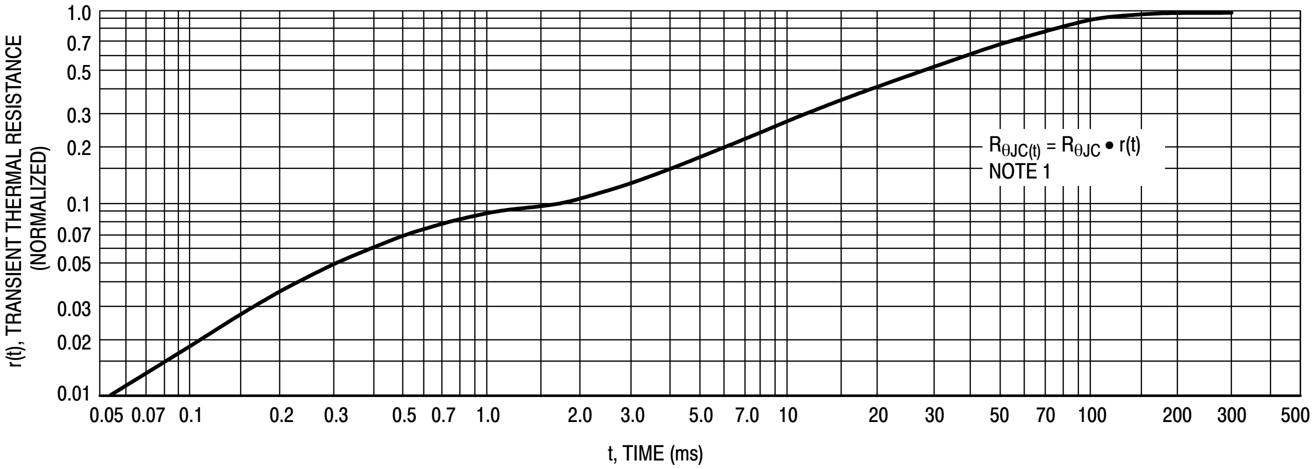
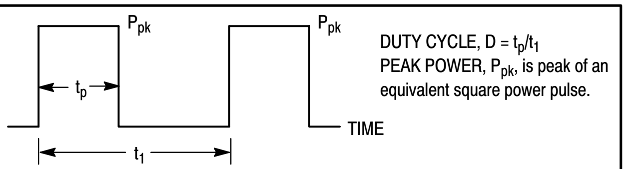


Figure 6. Thermal Response



To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see the outline drawing on page 1). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady–state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature, it may be determined by:

$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC}\,[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$ where

r(t) = normalized value of transient thermal resistance at time, t, from Figure 6, i.e.:

r $(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

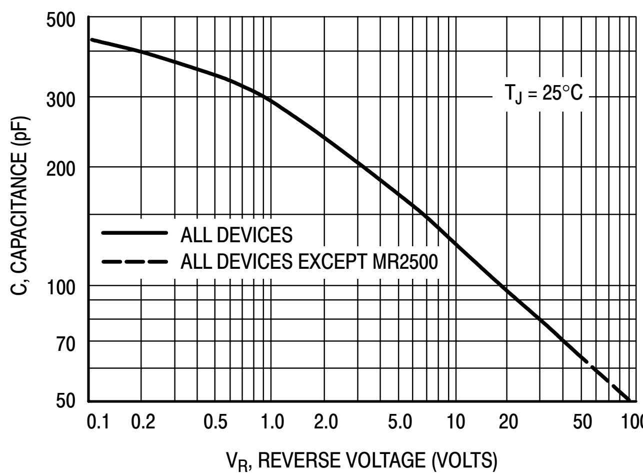


Figure 7. Capacitance

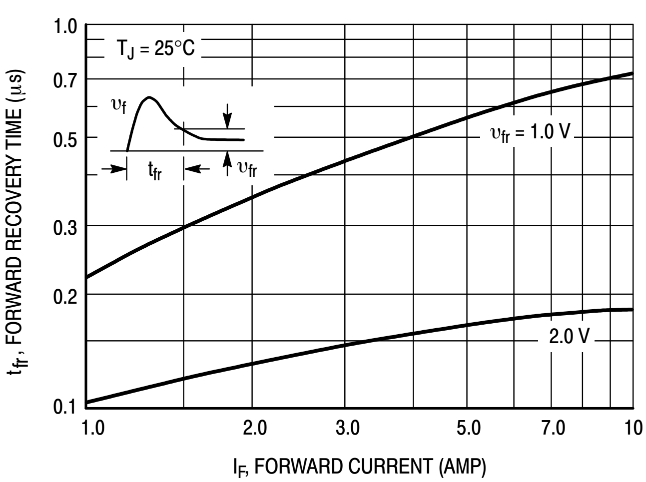


Figure 8. Forward Recovery Time

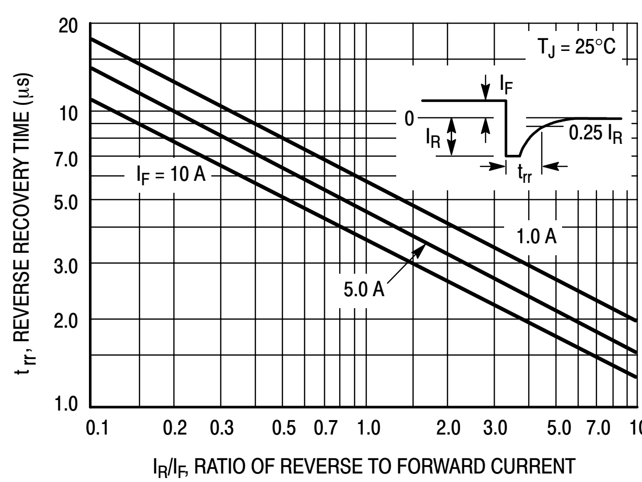


Figure 9. Reverse Recovery Time

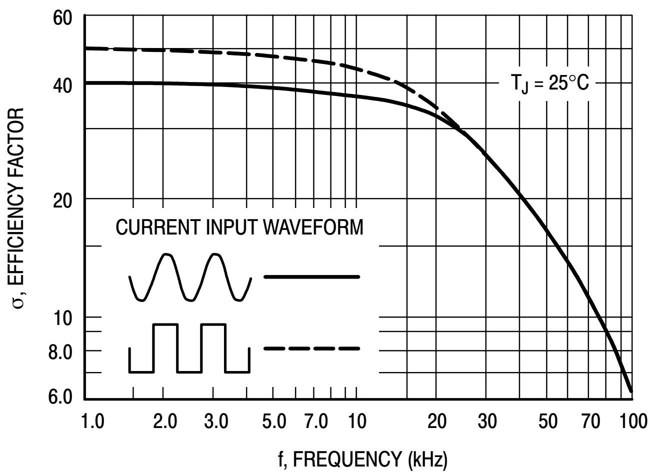


Figure 10. Rectification Waveform Efficiency

RECTIFICATION EFFICIENCY NOTE

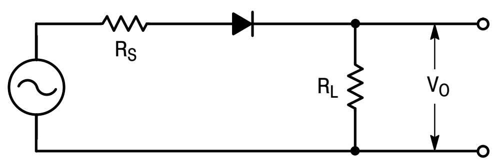


Figure 11. Single–Phase Half–Wave Rectifier Circuit

The rectification efficiency factor σ shown in Figure 10 was calculated using the formula:

$$\sigma = \frac{P_{(dc)}}{P_{(rms)}} = \frac{\frac{V^2{}_{o(dc)}}{R_L}}{\frac{V^2{}_{o(rms)}}{R_L}} \cdot 100\% = \frac{V^2{}_{o(dc)}}{V^2{}_{o(ac)} + V^2{}_{o(dc)}} \cdot 100\% \qquad (1)$$

For a sine wave input V_m sin (ωt) to the diode, assume lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{(sine)} = \frac{\frac{V^2{}_m}{\pi^2 R_L}}{\frac{V^2{}_m}{4R_L}} \cdot 100\% = \frac{4}{\pi^2} \cdot 100\% = 40.6\% \qquad (2)$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma_{(square)} = \frac{\frac{V^2{}_m}{2R_L}}{\frac{V^2{}_m}{R_L}} \cdot 100\% = 50\% \qquad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 9) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 10.

It should be emphasized that Figure 10 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_O with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 10.

ASSEMBLY AND SOLDERING INFORMATION

There are *two basic areas* of consideration for successful implementation of button rectifiers:

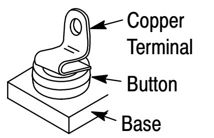
1. Mounting and Handling
2. Soldering

each should be carefully examined before attempting a finished assembly or mounting operation.

MOUNTING AND HANDLING

The button rectifier lends itself to a multitude of assembly arrangements but one key consideration must *always* be included:

One Side of the Connections to the Button Must Be Flexible!



This stress relief to the button should also be chosen for maximum contact area to afford the best heat transfer — but not at the expense of flexibility. For an annealed copper terminal a thickness of 0.015″ is suggested.

The base heat sink may be of various materials whose shape and size are a function of the individual application and the heat transfer requirements.

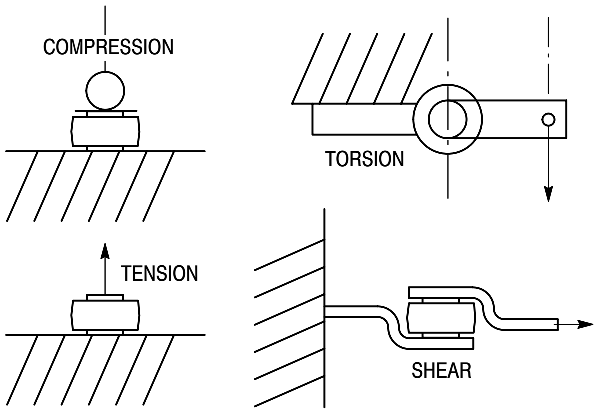
Common Materials	Advantages and Disadvantages
Steel	Low Cost; relatively low heat conductivity
Copper	High Cost; high heat conductivity
Aluminum	Medium Cost; medium heat conductivity Relatively expensive to plate and not all platers can process aluminum.

Handling of the button during assembly must be relatively gentle to minimize sharp impact shocks and avoid nicking of the plastic. Improperly designed automatic handling equipment is the worst source of unnecessary shocks. Techniques for vacuum handling and spring loading should be investigated.

The mechanical stress limits for the button diode are as follows:

Compression	32 lbs.	142.3 Newton
Tension	32 lbs.	142.3 Newton
Torsion	6–inch lbs.	0.68 Newton–meters
Shear	55 lbs.	244.7 Newton

MECHANICAL STRESS



Exceeding these recommended maximums can result in electrical degradation of the device.

SOLDERING

The button rectifier is basically a semiconductor chip bonded between two nickel–plated copper heat sinks with an encapsulating material of thermal–setting silicone. The exposed metal areas are also tin plated to enhance solderability.

In the soldering process it is important that the temperature not exceed 250°C if device damage is to be avoided. Various solder alloys can be used for this operation but two types are recommended for best results:

1. 95% Sn, 5% Sb; melting point 237°C
2. 96.5% tin, 3.5% silver; melting point 221°C
3. 63% tin, 37% lead; melting point 183°C

Solder is available as preforms or paste. The paste contains both the metal and flux and can be dispensed rapidly. The solder preform requires the application of a flux to assure good wetting of the solder. The type of flux used depends upon the degree of cleaning to be accomplished and is a function of the metals involved. These fluxes range from a mild rosin to a strong acid; e.g., Nickel plating oxides are best removed by an acid base flux while an activated rosin flux may be sufficient for tin plated parts.

Since the button is relatively light–weight, there is a tendency for it to float when the solder becomes liquid. To prevent bad joints and misalignment it is suggested that a weighting or spring loaded fixture be employed. It is also important that severe thermal shock (either heating or cooling) be avoided as it may lead to damage of the die or encapsulant of the part.

Button holding fixtures for use during soldering may be of various materials. Stainless steel has a longer use life while black anodized aluminum is less expensive and will limit heat reflection and enhance absorption. The assembly volume will influence the choice of materials. Fixture dimension tolerances for locating the button must allow for expansion during soldering as well as allowing for button clearance.

HEATING TECHNIQUES

The following four heating methods have their advantages and disadvantages depending on volume of buttons to be soldered.

1. **Belt Furnaces** readily handle large or small volumes and are adaptable to establishment of “on–line’’ assembly since a variable belt speed sets the run rate. Individual furnace zone controls make excellent temperature control possible.
2. **Flame Soldering** involves the directing of natural gas flame jets at the base of a heatsink as the heatsink is indexed to various loading–heating–cooling–unloading positions. This is the most economical labor method of soldering large volumes. Flame soldering offers good temperature control but requires sophisticated temperature monitoring systems such as infrared.

ASSEMBLY AND SOLDERING INFORMATION (continued)

3. **Ovens** are good for batch soldering and are production limited. There are handling problems because of slow cooling. Response time is load dependent, being a function of the watt rating of the oven and the mass of parts. Large ovens may not give an acceptable temperature gradient. Capital cost is low compared to belt furnaces and flame soldering.
4. **Hot Plates** are good for soldering small quantities of prototype devices. Temperature control is fair with overshoot common because of the exposed heating surface. Solder flow and positioning can be corrected during soldering since the assembly is exposed. Investment cost is very low.

Regardless of the heating method used, a soldering profile giving the time–temperature relationship of the particular method must be determined to assure proper soldering. Profiling must be performed on a scheduled basis to minimize poor soldering. The time–temperature relationship will change depending on the heating method used.

SOLDER PROCESS EVALUATION

Characteristics to look for when setting up the soldering process:

I **Overtemperature** is indicated by any one or all three of the following observations.

1. Remelting of the solder inside the button rectifier shows the temperature has exceeded 285°C and is noted by “islands’’ of shiny solder and solder dewetting when a unit is broken apart.
2. Cracked die inside the button may be observed by a moving reverse oscilloscope trace when pressure is applied to the unit.
3. Cracked plastic may be caused by thermal shock as well as overtemperature so cooling rate should also be checked.

II **Cold soldering** gives a grainy appearance and solder build–up without a smooth continuous solder fillet. The temperature must be adjusted until the proper solder fillet is obtained within the maximum temperature limits.

III **Incomplete solder fillets** result from insufficient solder or parts not making proper contact.

IV **Tilted buttons** can cause a void in the solder between the heatsink and button rectifier which will result in poor heat transfer during operation. An eight degree tilt is a suggested maximum value.

V **Plating problems** require a knowledge of plating operations for complete understanding of observed deficiencies.

1. Peeling or plating separation is generally seen when a button is broken away for solder inspection. If heatsink or terminal base metal is present the plating is poor and must be corrected.
2. Thin plating allows the solder to penetrate through to the base metal and can give a poor connection. A suggested minimum plating thickness is 300 microinches.
3. Contaminated soldering surfaces may out–gas and cause non–wetting resulting in voids in the solder connection. The exact cause is not always readily apparent and can be because of:
   (a) improper plating
   (b) mishandling of parts
   (c) improper and/or excessive storage time

SOLDER PROCESS MONITORING

Continuous monitoring of the soldering process must be established to minimize potential problems. All parts used in the soldering operation should be sampled on a lot by lot basis by assembly of a controlled sample. Evaluate the control sample by break–apart tests to view the solder connections, by physical strength tests and by dimensional characteristics for part mating.

A shear test is a suggested way of testing the solder bond strength.

POST SOLDERING OPERATION CONSIDERATIONS

After soldering, the completed assembly must be unloaded, washed and inspected.

Unloading must be done carefully to avoid unnecessary stress. Assembly fixtures should be cooled to room temperature so solder profiles are not affected.

Washing is mandatory if an acid flux is used because of its ionic and corrosive nature. Wash the assemblies in agitated hot water and detergent for three to five minutes. After washing; rinse, blow off excessive water and bake 30 minutes at 150°C to remove trapped moisture.

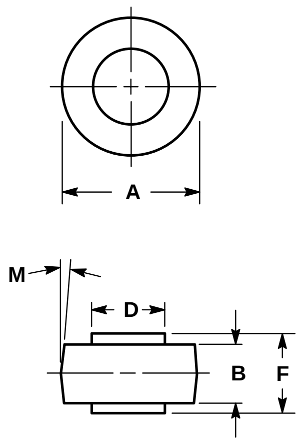
Inspection should be both electrical and physical. Any rejects can be reworked as required.

SUMMARY

The Button Rectifier is an excellent building block for specialized applications. The prime example of its use is the output bridge of the automative alternator where millions are used each year. Although the material presented here is not all inclusive, primary considerations for use are presented. For further information, contact the nearest ON Semiconductor Sales Office or franchised distributor.

PACKAGE DIMENSIONS

MICRODE BUTTON
CASE 193–04
ISSUE J



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.43	8.69	0.332	0.342
B	4.19	4.45	0.165	0.175
D	5.54	5.64	0.218	0.222
F	5.94	6.25	0.234	0.246
M	5° NOM		5° NOM	

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